Giovanni Isella graduated in Nuclear Engineering at the Politecnico di Milano, Italy in 1997 and holds a Ph.D. in Physics from the same institution. Between 2001 and 2002 G. I. has been working on the deposition and characterization of silicongermanium heterostructures at the ETH-Zürich. In 2002 he obtained a faculty researcher position at the Physics Department of the Politecnico di Milano-Italy where he continued to work in the field of SiGe epitaxy. Since 2007 he is leading the SiGe epitaxy team at the laboratory for nanostructures epitaxy and spintronics on silicon (LNESS-Politecnico di Milano). In 2014 he became Associate Professor at Polimi and in 2017 the director of the laboratory for nanostructures, epitaxy and spintronics on silicon (LNESS). His current interests and expertise include: spin dynamics in Ge quantum wells, infrared light detection and modulation in SiGe heterostructures, Ge deposition on patterned substrates, integration of III-V semiconductors on Ge/Si, SiGe heterostructuctures for thermoelectric power generation. Since 2017 he is the director of the LNESS centre.